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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	72MHz
Connectivity	CANbus, EBI/EMI, I ² C, IrDA, SPI, UART/USART
Peripherals	DMA, I ² S, LVD, POR, PWM, WDT
Number of I/O	44
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 26x16b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mk10dx128vlh7

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong



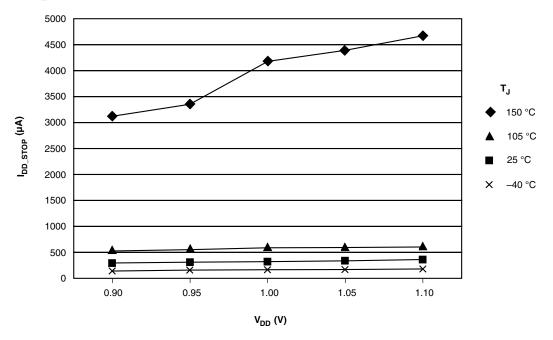
3.8.1 Example 1

This is an example of an operating behavior that includes a typical value:

Symbol	Description	Min.	Тур.	Max.	Unit
I _{WP}	Digital I/O weak pullup/pulldown current	10	70	130	μΑ

3.8.2 Example 2

This is an example of a chart that shows typical values for various voltage and temperature conditions:



3.9 Typical value conditions

Typical values assume you meet the following conditions (or other conditions as specified):

Symbol	Description	Value	Unit
T _A	Ambient temperature	25	C°
V _{DD}	3.3 V supply voltage	3.3	V



5.2.3	Voltage and current operating behaviors				
	Table 4. Voltage and current operating behaviors				

Symbol	Description	Min.	Max.	Unit	Notes
V _{OH}	Output high voltage — high drive strength				
	• 2.7 V \leq V _{DD} \leq 3.6 V, I _{OH} = -9mA	V _{DD} – 0.5	_	V	
	• 1.71 V \leq V _{DD} \leq 2.7 V, I _{OH} = -3mA	V _{DD} – 0.5	_	V	
	Output high voltage — low drive strength				
	• 2.7 V \leq V _{DD} \leq 3.6 V, I _{OH} = -2mA	V _{DD} – 0.5	—	V	
	• 1.71 V \leq V _{DD} \leq 2.7 V, I _{OH} = -0.6mA	V _{DD} – 0.5	—	V	
I _{OHT}	Output high current total for all ports		100	mA	
V _{OL}	Output low voltage — high drive strength				
	• 2.7 V \leq V _{DD} \leq 3.6 V, I _{OL} = 9mA		0.5	V	
	• 1.71 V \leq V _{DD} \leq 2.7 V, I _{OL} = 3mA	_	0.5	V	
	Output low voltage — low drive strength				
	• 2.7 V \leq V _{DD} \leq 3.6 V, I _{OL} = 2mA		0.5	V	
	• 1.71 V \leq V _{DD} \leq 2.7 V, I _{OL} = 0.6mA	_	0.5	V	
I _{OLT}	Output low current total for all ports	_	100	mA	
I _{IN}	Input leakage current (per pin) for full temperature range	—	1	μA	1
I _{IN}	Input leakage current (per pin) at 25°C	—	0.025	μA	1
I _{OZ}	Hi-Z (off-state) leakage current (per pin)	—	1	μA	
R _{PU}	Internal pullup resistors	20	50	kΩ	2
R _{PD}	Internal pulldown resistors	20	50	kΩ	3

1. Measured at VDD=3.6V

2. Measured at V_{DD} supply voltage = V_{DD} min and Vinput = V_{SS}

3. Measured at V_{DD} supply voltage = V_{DD} min and Vinput = V_{DD}

5.2.4 Power mode transition operating behaviors

All specifications except t_{POR} , and VLLSx \rightarrow RUN recovery times in the following table assume this clock configuration:

- CPU and system clocks = 72 MHz
- Bus clock = 36 MHz
- FlexBus clock = 36 MHz
- Flash clock = 24 MHz



Symbol	Description	Min.	Тур.	Max.	Unit	Notes
I _{DD_VLPW}	Very-low-power wait mode current at 3.0 V — all peripheral clocks disabled	_	0.61		mA	8
I _{DD_STOP}	Stop mode current at 3.0 V					
	• @ -40 to 25°C	—	0.35	0.567	mA	
	• @ 70°C		0.384	0.793	mA	
	• @ 105°C	_	0.628	1.2	mA	
I _{DD_VLPS}	Very-low-power stop mode current at 3.0 V					
	• @ -40 to 25°C		5.9	32.7	μA	
	• @ 70°C	_	26.1	59.8	μA	
	• @ 105°C	_	98.1	188	μA	
I _{DD_LLS}	Low leakage stop mode current at 3.0 V					9
	• @ -40 to 25°C		2.6	8.6	μA	
	• @ 70°C	_	10.3	29.1	μA	
	• @ 105°C	—	42.5	92.5	μA	
IDD_VLLS3	Very low-leakage stop mode 3 current at 3.0 V					9
	• @ -40 to 25°C		1.9	5.8	μA	
	• @ 70°C	_	6.9	12.1	μA	
	• @ 105°C	_	28.1	41.9	μA	
IDD_VLLS2	Very low-leakage stop mode 2 current at 3.0 V					
	• @ -40 to 25°C	_	1.59	5.5	μA	
	• @ 70°C		4.3	9.5	μA	
	• @ 105°C	_	17.5	34	μA	
I _{DD_VLLS1}	Very low-leakage stop mode 1 current at 3.0 V					
	• @ -40 to 25°C	_	1.47	5.4	μA	
	• @ 70°C	_	2.97	8.1	μA	
	• @ 105°C	_	12.41	32	μA	
I _{DD_VBAT}	Average current with RTC and 32kHz disabled at 3.0 V				<u> </u>	
	• @ -40 to 25°C		0.19	0.22	μA	
	• @ 70°C	_	0.19	0.64	μΑ	
	• @ 105°C		2.2	3.2	μΑ	

Table 6. Power consumption operating behaviors (continued)

Table continues on the next page ...



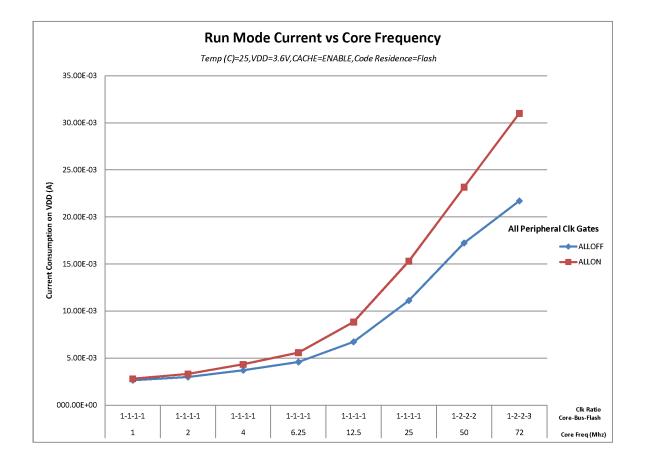


Figure 2. Run mode supply current vs. core frequency





5.3 Switching specifications

5.3.1 Device clock specifications

Table 8. Device clock specifications

Symbol	Description	Min.	Max.	Unit	Notes
	Normal run me	ode	•	•	
f _{SYS}	System and core clock	_	72	MHz	
f _{BUS}	Bus clock	_	50	MHz	
FB_CLK	FlexBus clock	_	50	MHz	
f _{FLASH}	Flash clock		25	MHz	
f _{LPTMR}	LPTMR clock	_	25	MHz	
	VLPR mode	,1			
f _{SYS}	System and core clock	_	4	MHz	
f _{BUS}	Bus clock	_	4	MHz	
FB_CLK	FlexBus clock	—	4	MHz	
f _{FLASH}	Flash clock	_	0.5	MHz	
f _{ERCLK}	External reference clock	_	16	MHz	
f _{LPTMR_pin}	LPTMR clock	_	25	MHz	
f _{LPTMR_ERCLK}	LPTMR external reference clock	_	16	MHz	
f _{FlexCAN_ERCLK}	FlexCAN external reference clock	—	8	MHz	
f _{I2S_MCLK}	I2S master clock	_	12.5	MHz	
f _{I2S_BCLK}	I2S bit clock	—	4	MHz	

1. The frequency limitations in VLPR mode here override any frequency specification listed in the timing specification for any other module.

5.3.2 General switching specifications

These general purpose specifications apply to all signals configured for GPIO, UART, CAN, CMT, and I²C signals.

Symbol	Description	Min.	Max.	Unit	Notes
	GPIO pin interrupt pulse width (digital glitch filter disabled) — Synchronous path	1.5	_	Bus clock cycles	1, 2
	GPIO pin interrupt pulse width (digital glitch filter disabled, analog filter enabled) — Asynchronous path	100	—	ns	3

 Table 9. General switching specifications

Table continues on the next page ...



Symbol	Description	Min.	Max.	Unit	Notes
	GPIO pin interrupt pulse width (digital glitch filter disabled, analog filter disabled) — Asynchronous path	16	-	ns	3
	External reset pulse width (digital glitch filter disabled)	100	_	ns	3
	Mode select (EZP_CS) hold time after reset deassertion	2	-	Bus clock cycles	
	Port rise and fall time (high drive strength)				4
	Slew disabled				
	• $1.71 \le V_{DD} \le 2.7V$	—	12	ns	
	• $2.7 \le V_{DD} \le 3.6V$	_	6	ns	
	Slew enabled				
	• $1.71 \le V_{DD} \le 2.7V$	_	36	ns	
	• $2.7 \le V_{DD} \le 3.6V$	_	24	ns	
	Port rise and fall time (low drive strength)				5
	Slew disabled				
	• $1.71 \le V_{DD} \le 2.7V$	_	12	ns	
	• $2.7 \le V_{DD} \le 3.6V$	_	6	ns	
	Slew enabled				
	• 1.71 ≤ V _{DD} ≤ 2.7V	_	36	ns	
	• $2.7 \le V_{DD} \le 3.6V$	—	24	ns	

Table 9. General switching specifications (continued)

- 1. This is the minimum pulse width that is guaranteed to pass through the pin synchronization circuitry. Shorter pulses may or may not be recognized. In Stop, VLPS, LLS, and VLLSx modes, the synchronizer is bypassed so shorter pulses can be recognized in that case.
- 2. The greater synchronous and asynchronous timing must be met.
- 3. This is the minimum pulse width that is guaranteed to be recognized as a pin interrupt request in Stop, VLPS, LLS, and VLLSx modes.
- 4. 75pF load
- 5. 15pF load

5.4 Thermal specifications

5.4.1 Thermal operating requirements

Table 10. Thermal operating requirements

Symbol	Description	Min.	Max.	Unit
TJ	Die junction temperature	-40	125	°C
T _A	Ambient temperature	-40	105	°C



Symbol	Description	Min.	Max.	Unit
J1	TCLK frequency of operation			MHz
	Boundary Scan	0	10	
	JTAG and CJTAG	0	25	
	Serial Wire Debug	0	50	
J2	TCLK cycle period	1/J1		ns
J3	TCLK clock pulse width			
	Boundary Scan	50	_	ns
	JTAG and CJTAG	20	_	ns
	Serial Wire Debug	10	_	ns
J4	TCLK rise and fall times		3	ns
J5	Boundary scan input data setup time to TCLK rise	20		ns
J6	Boundary scan input data hold time after TCLK rise	0		ns
J7	TCLK low to boundary scan output data valid	—	25	ns
J8	TCLK low to boundary scan output high-Z	_	25	ns
J9	TMS, TDI input data setup time to TCLK rise	8		ns
J10	TMS, TDI input data hold time after TCLK rise	1	_	ns
J11	TCLK low to TDO data valid	—	17	ns
J12	TCLK low to TDO high-Z	—	17	ns
J13	TRST assert time	100	—	ns
J14	TRST setup time (negation) to TCLK high	8		ns

Table 12.	JTAG limited	voltage ran	ge electricals	(continued))
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Table 13. JTAG full voltage range electricals

Symbol	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
J1	TCLK frequency of operation			MHz
	Boundary Scan	0	10	
	JTAG and CJTAG	0	20	
	Serial Wire Debug	0	40	
J2	TCLK cycle period	1/J1		ns
JЗ	TCLK clock pulse width			
	Boundary Scan	50	_	ns
	JTAG and CJTAG	25	_	ns
	Serial Wire Debug	12.5	—	ns
J4	TCLK rise and fall times		3	ns
J5	Boundary scan input data setup time to TCLK rise	20	_	ns
J6	Boundary scan input data hold time after TCLK rise	0		ns

Table continues on the next page ...



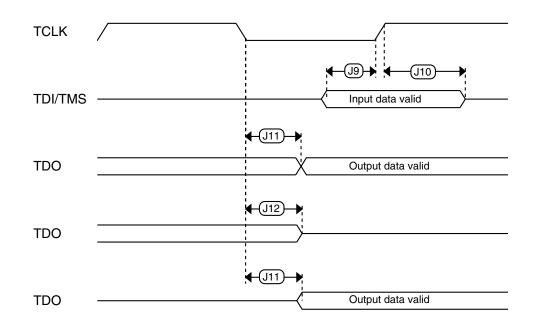
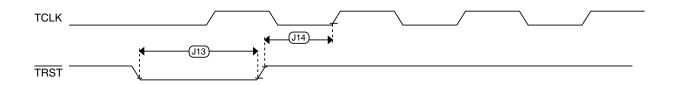


Figure 8. Test Access Port timing





6.2 System modules

There are no specifications necessary for the device's system modules.

6.3 Clock modules



Symbol	Description	Min.	Тур.	Max.	Unit	Notes
J _{cyc_fll}	FLL period jitter	_	180	_	ps	
	 f_{VCO} = 48 MHz f_{VCO} = 98 MHz 	_	150	_		
t _{fll_acquire}	FLL target frequency acquisition time	_	—	1	ms	6
	P	ĹĹ				
f _{vco}	VCO operating frequency	48.0	—	100	MHz	
I _{pll}	PLL operating current • PLL @ 96 MHz (f _{osc_hi_1} = 8 MHz, f _{pll_ref} = 2 MHz, VDIV multiplier = 48)	_	1060	_	μΑ	7
I _{pll}	PLL operating current • PLL @ 48 MHz (f _{osc_hi_1} = 8 MHz, f _{pll_ref} = 2 MHz, VDIV multiplier = 24)	_	600	-	μA	7
f _{pll_ref}	PLL reference frequency range	2.0	_	4.0	MHz	
J _{cyc_pll}	PLL period jitter (RMS)					8
	• f _{vco} = 48 MHz	_	120		ps	
	• f _{vco} = 100 MHz	_	50	_	ps	
J _{acc_pll}	PLL accumulated jitter over 1µs (RMS)					8
	• f _{vco} = 48 MHz	_	1350		ps	
	• f _{vco} = 100 MHz	_	600	_	ps	
D _{lock}	Lock entry frequency tolerance	± 1.49	—	± 2.98	%	
D _{unl}	Lock exit frequency tolerance	± 4.47	—	± 5.97	%	
t _{pll_lock}	Lock detector detection time	_	_	$150 \times 10^{-6} + 1075(1/ f_{pll_ref})$	S	9

Table 14. MCG specifications (continued)

1. This parameter is measured with the internal reference (slow clock) being used as a reference to the FLL (FEI clock mode).

- 2. These typical values listed are with the slow internal reference clock (FEI) using factory trim and DMX32=0.
- The resulting system clock frequencies should not exceed their maximum specified values. The DCO frequency deviation
 (Δf_{dco t}) over voltage and temperature should be considered.
- 4. These typical values listed are with the slow internal reference clock (FEI) using factory trim and DMX32=1.
- 5. The resulting clock frequency must not exceed the maximum specified clock frequency of the device.
- 6. This specification applies to any time the FLL reference source or reference divider is changed, trim value is changed, DMX32 bit is changed, DRS bits are changed, or changing from FLL disabled (BLPE, BLPI) to FLL enabled (FEI, FEE, FBE, FBI). If a crystal/resonator is being used as the reference, this specification assumes it is already running.
- 7. Excludes any oscillator currents that are also consuming power while PLL is in operation.
- 8. This specification was obtained using a Freescale developed PCB. PLL jitter is dependent on the noise characteristics of each PCB and results will vary.
- This specification applies to any time the PLL VCO divider or reference divider is changed, or changing from PLL disabled (BLPE, BLPI) to PLL enabled (PBE, PEE). If a crystal/resonator is being used as the reference, this specification assumes it is already running.

6.3.2 Oscillator electrical specifications

This section provides the electrical characteristics of the module.



rempheral operating requirements and behaviors

4. Crystal startup time is defined as the time between the oscillator being enabled and the OSCINIT bit in the MCG_S register being set.

NOTE

The 32 kHz oscillator works in low power mode by default and cannot be moved into high power/gain mode.

6.3.3 32 kHz Oscillator Electrical Characteristics

This section describes the module electrical characteristics.

6.3.3.1 32 kHz oscillator DC electrical specifications Table 17. 32kHz oscillator DC electrical specifications

Symbol	Description	Min.	Тур.	Max.	Unit
V _{BAT}	Supply voltage	1.71	—	3.6	V
R _F	Internal feedback resistor	_	100	_	MΩ
C _{para}	Parasitical capacitance of EXTAL32 and XTAL32	_	5	7	pF
V _{pp} ¹	Peak-to-peak amplitude of oscillation		0.6		V

1. When a crystal is being used with the 32 kHz oscillator, the EXTAL32 and XTAL32 pins should only be connected to required oscillator components and must not be connected to any other devices.

6.3.3.2 32kHz oscillator frequency specifications Table 18. 32kHz oscillator frequency specifications

Symbol	ol Description		Тур.	Max.	Unit	Notes
f _{osc_lo}	Oscillator crystal	—	32.768	—	kHz	
t _{start}	tart Crystal start-up time		1000	_	ms	1
V _{ec_extal32}	Externally provided input clock amplitude	700	_	V _{BAT}	mV	2, 3

1. Proper PC board layout procedures must be followed to achieve specifications.

2. This specification is for an externally supplied clock driven to EXTAL32 and does not apply to any other clock input. The oscillator remains enabled and XTAL32 must be left unconnected.

3. The parameter specified is a peak-to-peak value and V_{IH} and V_{IL} specifications do not apply. The voltage of the applied clock must be within the range of V_{SS} to V_{BAT} .

6.4 Memories and memory interfaces

6.4.1 Flash electrical specifications

This section describes the electrical characteristics of the flash memory module.



Peripheral operating requirements and behaviors

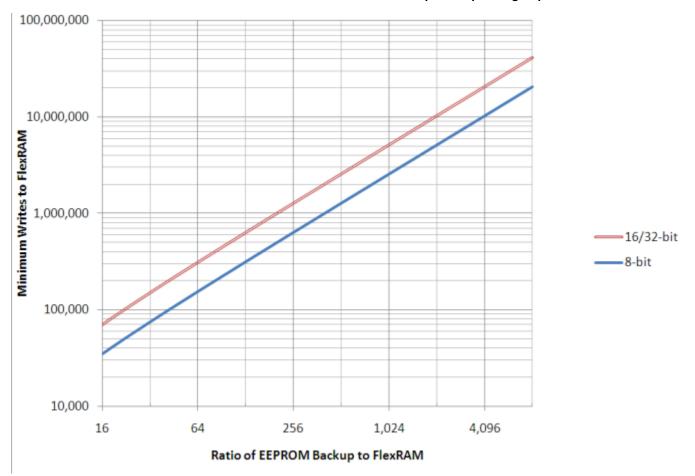


Figure 10. EEPROM backup writes to FlexRAM

6.4.2 EzPort Switching Specifications Table 23. EzPort switching specifications

Num	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
EP1	EZP_CK frequency of operation (all commands except READ)	-	f _{SYS} /2	MHz
EP1a	EZP_CK frequency of operation (READ command)	_	f _{SYS} /8	MHz
EP2	EZP_CS negation to next EZP_CS assertion	2 x t _{EZP_CK}	—	ns
EP3	EZP_CS input valid to EZP_CK high (setup)	5		ns
EP4	EZP_CK high to EZP_CS input invalid (hold)	5		ns
EP5	EZP_D input valid to EZP_CK high (setup)	2		ns
EP6	EZP_CK high to EZP_D input invalid (hold)	5	—	ns
EP7	EZP_CK low to EZP_Q output valid	_	16	ns
EP8	EZP_CK low to EZP_Q output invalid (hold)	0	—	ns
EP9	EZP_CS negation to EZP_Q tri-state	_	12	ns



2. Specification is valid for all FB_AD[31:0] and $\overline{FB_TA}$.

Table 25. Flexbus full voltage range switching specification
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Num	Description	Min.	Max.	Unit	Notes
	Operating voltage	1.71	3.6	V	
	Frequency of operation		FB_CLK	MHz	
FB1	Clock period	1/FB_CLK	_	ns	
FB2	Address, data, and control output valid	—	13.5	ns	1
FB3	Address, data, and control output hold	0	—	ns	1
FB4	Data and FB_TA input setup	13.7	_	ns	2
FB5	Data and FB_TA input hold	0.5		ns	2

1. Specification is valid for all FB_AD[31:0], FB_BE/BWEn, FB_CSn, FB_OE, FB_R/W, FB_TBST, FB_TSIZ[1:0], FB_ALE, and FB_TS.

2. Specification is valid for all FB_AD[31:0] and $\overline{FB_TA}$.



Peripheral operating requirements and behaviors

Symbol	Description	Conditions	Min.	Typ. ¹	Max.	Unit	Notes
C _{rate}	ADC conversion rate	16-bit mode					5
	Tale	No ADC hardware averaging	37.037	—	461.467	Ksps	
		Continuous conversions enabled, subsequent conversion time					

Table 26. 16-bit ADC operating conditions (continued)

- 1. Typical values assume V_{DDA} = 3.0 V, Temp = 25 °C, f_{ADCK} = 1.0 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.
- 2. DC potential difference.
- 3. This resistance is external to MCU. The analog source resistance must be kept as low as possible to achieve the best results. The results in this data sheet were derived from a system which has < 8 Ω analog source resistance. The R_{AS}/C_{AS} time constant should be kept to < 1ns.
- 4. To use the maximum ADC conversion clock frequency, the ADHSC bit must be set and the ADLPC bit must be clear.
- 5. For guidelines and examples of conversion rate calculation, download the ADC calculator tool

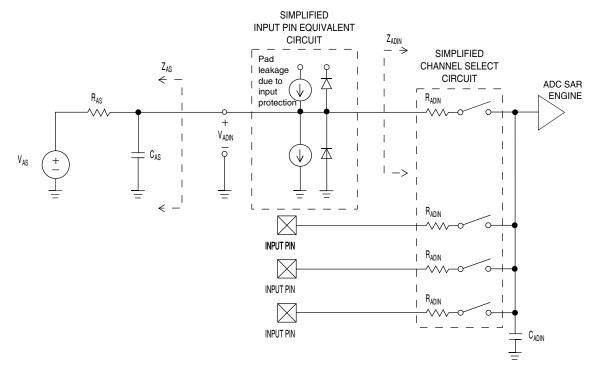


Figure 14. ADC input impedance equivalency diagram

6.6.1.2 16-bit ADC electrical characteristics Table 27. 16-bit ADC characteristics (V_{REFH} = V_{DDA}, V_{REFL} = V_{SSA})

Symbol	Description	Conditions ¹	Min.	Typ. ²	Max.	Unit	Notes
I _{DDA_ADC}	Supply current		0.215		1.7	mA	3

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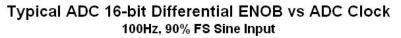


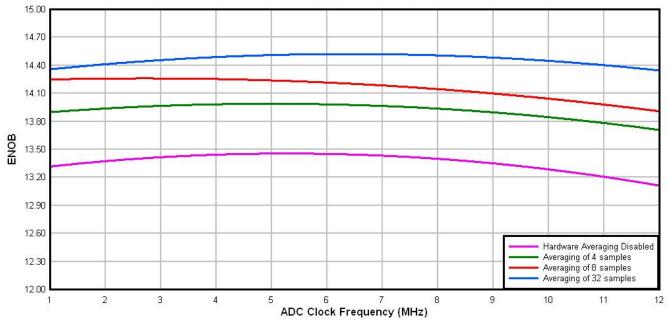
Table 27.	16-bit ADC characteristics	$(V_{REFH} = V_D$	$D_{A}, V_{REFL} =$	V _{SSA}) (continued)
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Symbol	Description	Conditions ¹	Min.	Typ. ²	Max.	Unit	Notes
EL	Input leakage error		$I_{ln} \times R_{AS}$			mV	I _{In} = leakage current
							(refer to the MCU's voltage and current operating ratings)
	Temp sensor slope	Across the full temperature range of the device	_	1.715	_	mV/°C	
V _{TEMP25}	Temp sensor voltage	25 °C	-	719		mV	

1. All accuracy numbers assume the ADC is calibrated with $V_{REFH} = V_{DDA}$

- Typical values assume V_{DDA} = 3.0 V, Temp = 25°C, f_{ADCK} = 2.0 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.
- The ADC supply current depends on the ADC conversion clock speed, conversion rate and the ADLPC bit (low power). For lowest power operation the ADLPC bit must be set, the HSC bit must be clear with 1 MHz ADC conversion clock speed.
- 4. 1 LSB = $(V_{REFH} V_{REFL})/2^N$
- 5. ADC conversion clock < 16 MHz, Max hardware averaging (AVGE = %1, AVGS = %11)
- 6. Input data is 100 Hz sine wave. ADC conversion clock < 12 MHz.
- 7. Input data is 1 kHz sine wave. ADC conversion clock < 12 MHz.









Peripheral operating requirements and behaviors

Symbol	Description	Conditions	Min.	Typ. ¹	Max.	Unit	Notes
C _{rate}	ADC conversion	≤ 13 bit modes	18.484	_	450	Ksps	7
	rate	No ADC hardware averaging					
		Continuous conversions enabled					
		Peripheral clock = 50 MHz					
		16 bit modes	37.037	_	250	Ksps	8
		No ADC hardware averaging					
		Continuous conversions enabled					
		Peripheral clock = 50 MHz					

Table 28. 16-bit ADC with PGA operating conditions (continued)

- 1. Typical values assume V_{DDA} = 3.0 V, Temp = 25°C, f_{ADCK} = 6 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.
- 2. ADC must be configured to use the internal voltage reference (VREF_OUT)
- 3. PGA reference is internally connected to the VREF_OUT pin. If the user wishes to drive VREF_OUT with a voltage other than the output of the VREF module, the VREF module must be disabled.
- 4. For single ended configurations the input impedance of the driven input is R_{PGAD}/2
- 5. The analog source resistance (R_{AS}), external to MCU, should be kept as minimum as possible. Increased R_{AS} causes drop in PGA gain without affecting other performances. This is not dependent on ADC clock frequency.
- 6. The minimum sampling time is dependent on input signal frequency and ADC mode of operation. A minimum of 1.25µs time should be allowed for Fin=4 kHz at 16-bit differential mode. Recommended ADC setting is: ADLSMP=1, ADLSTS=2 at 8 MHz ADC clock.
- 7. ADC clock = 18 MHz, ADLSMP = 1, ADLST = 00, ADHSC = 1
- 8. ADC clock = 12 MHz, ADLSMP = 1, ADLST = 01, ADHSC = 1

6.6.1.4 16-bit ADC with PGA characteristics with Chop enabled (ADC PGA[PGACHPb] =0)

Table 29. 16-bit ADC with PGA characteristics

Symbol	Description	Conditions	Min.	Typ. ¹	Max.	Unit	Notes
I _{DDA_PGA}	Supply current	Low power (ADC_PGA[PGALPb]=0)		420	644	μA	2
I _{DC_PGA}	Input DC current		$\frac{2}{R_{\rm PGAD}} \left(\frac{(V_{\rm REFPGA} \times 0.583) - V_{\rm CM}}{({\rm Gain+l})} \right)$			A	3
		Gain =1, V _{REFPGA} =1.2V, V _{CM} =0.5V	_	1.54	—	μA	
		Gain =64, V_{REFPGA} =1.2V, V_{CM} =0.1V	_	0.57		μA	

Table continues on the next page ...

rempheral operating requirements and behaviors

6.6.3.2 12-bit DAC operating behaviors Table 32. 12-bit DAC operating behaviors

Symbol	Description	Min.	Тур.	Max.	Unit	Notes	
I _{DDA_DACL}	Supply current — low-power mode		—	150	μΑ		
I _{DDA_DACH} P	Supply current — high-speed mode	—	—	700	μΑ		
t _{DACLP}	Full-scale settling time (0x080 to 0xF7F) — low-power mode	_	100	200	μs	1	
t _{DACHP}	Full-scale settling time (0x080 to 0xF7F) — high-power mode	—	15	30	μs	1	
t _{CCDACLP}	Code-to-code settling time (0xBF8 to 0xC08) — low-power mode and high-speed mode	—	0.7	1	μs	1	
V _{dacoutl}	DAC output voltage range low — high-speed mode, no load, DAC set to 0x000	_	—	100	mV		
V _{dacouth}	DAC output voltage range high — high- speed mode, no load, DAC set to 0xFFF	V _{DACR} -100	—	V _{DACR}	mV		
INL	Integral non-linearity error — high speed mode	—	—	±8	LSB	2	
DNL	Differential non-linearity error — V _{DACR} > 2 V	_	—	±1	LSB	3	
DNL	Differential non-linearity error — V _{DACR} = VREF_OUT	_	—	±1	LSB	4	
V _{OFFSET}	Offset error	_	±0.4	±0.8	%FSR	5	
E _G	Gain error	_	±0.1	±0.6	%FSR	5	
PSRR	Power supply rejection ratio, $V_{DDA} \ge 2.4 V$	60	—	90	dB		
T _{CO}	Temperature coefficient offset voltage	_	3.7	—	μV/C	6	
T_{GE}	Temperature coefficient gain error	_	0.000421	_	%FSR/C		
Rop	Output resistance load = $3 \text{ k}\Omega$	—	—	250	Ω		
SR	Slew rate -80h \rightarrow F7Fh \rightarrow 80h				V/µs		
	 High power (SP_{HP}) 	1.2	1.7	—			
	 Low power (SP_{LP}) 	0.05	0.12	—			
СТ	Channel to channel cross talk	_		-80	dB		
BW	3dB bandwidth				kHz		
	• High power (SP _{HP})	550	_	_			
	Low power (SP _{LP})	40	_	—			

1. Settling within ±1 LSB

- 2. The INL is measured for 0 + 100 mV to V_{DACR} –100 mV
- 3. The DNL is measured for 0 + 100 mV to V_{DACR} –100 mV
- 4. The DNL is measured for 0 + 100 mV to V_{DACR} –100 mV with V_{DDA} > 2.4 V
- 5. Calculated by a best fit curve from V_{SS} + 100 mV to V_{DACR} 100 mV
- V_{DDA} = 3.0 V, reference select set for V_{DDA} (DACx_CO:DACRFS = 1), high power mode (DACx_CO:LPEN = 0), DAC set to 0x800, temperature range is across the full range of the device



Symbol	Description	Min.	Тур.	Max.	Unit	Notes
V _{out}	Voltage reference output with factory trim at nominal V_{DDA} and temperature=25C	1.1915	1.195	1.1977	V	
V _{out}	Voltage reference output — factory trim	1.1584	_	1.2376	V	
V _{out}	Voltage reference output — user trim	1.193	_	1.197	V	
V _{step}	Voltage reference trim step	—	0.5	—	mV	
V _{tdrift}	Temperature drift (Vmax -Vmin across the full temperature range)	_		80	mV	
I _{bg}	Bandgap only current	—	_	80	μA	1
I _{lp}	Low-power buffer current	—	—	360	uA	1
I _{hp}	High-power buffer current	—	_	1	mA	1
ΔV_{LOAD}	Load regulation				μV	1, 2
	• current = ± 1.0 mA	_	200	_		
T _{stup}	Buffer startup time	—		100	μs	
V _{vdrift}	ft Voltage drift (Vmax -Vmin across the full voltage range)		2	_	mV	1

Table 34. VREF full-range operating behaviors

1. See the chip's Reference Manual for the appropriate settings of the VREF Status and Control register.

2. Load regulation voltage is the difference between the VREF_OUT voltage with no load vs. voltage with defined load

Table 35. VREF limited-range operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
T _A	Temperature	0	50	°C	

Table 36. VREF limited-range operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
V _{out}	Voltage reference output with factory trim	1.173	1.225	V	

6.7 Timers

See General switching specifications.

6.8 Communication interfaces



Table 42. I2S/SAI slave mode timing in Normal Run, Wait and Stop modes (full voltage range) (continued)

Num.	Characteristic	Min.	Max.	Unit
S13	I2S_TX_FS/I2S_RX_FS input setup before I2S_TX_BCLK/I2S_RX_BCLK	5.8	-	ns
S14	I2S_TX_FS/I2S_RX_FS input hold after I2S_TX_BCLK/I2S_RX_BCLK	2	-	ns
S16	I2S_TX_BCLK to I2S_TXD/I2S_TX_FS output invalid	0	—	ns
S17	I2S_RXD setup before I2S_RX_BCLK	5.8	—	ns
S18	I2S_RXD hold after I2S_RX_BCLK	2	—	ns
S19	I2S_TX_FS input assertion to I2S_TXD output valid ¹	—	25	ns

1. Applies to first bit in each frame and only if the TCR4[FSE] bit is clear

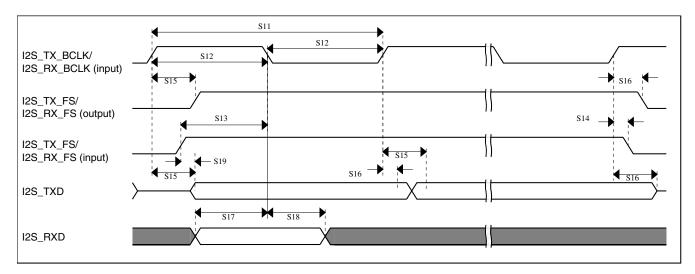


Figure 26. I2S/SAI timing — slave modes

6.8.6.2 VLPR, VLPW, and VLPS mode performance over the full operating voltage range

This section provides the operating performance over the full operating voltage for the device in VLPR, VLPW, and VLPS modes.

Table 43. I2S/SAI master mode timing in VLPR, VLPW, and VLPS modes
(full voltage range)

Num.	Characteristic	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
S1	I2S_MCLK cycle time	62.5	—	ns
S2	I2S_MCLK pulse width high/low	45%	55%	MCLK period
S3	I2S_TX_BCLK/I2S_RX_BCLK cycle time (output)	250	—	ns
S4	I2S_TX_BCLK/I2S_RX_BCLK pulse width high/low	45%	55%	BCLK period

Table continues on the next page...



r mout

64 LQFP _QFN	Pin Name	Default	ALTO	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	EzPort
18	DAC0_OUT/ CMP1_IN3/ ADC0_SE23	DAC0_OUT/ CMP1_IN3/ ADC0_SE23	DAC0_OUT/ CMP1_IN3/ ADC0_SE23								
19	XTAL32	XTAL32	XTAL32								
20	EXTAL32	EXTAL32	EXTAL32								
21	VBAT	VBAT	VBAT								
22	PTA0	JTAG_TCLK/ SWD_CLK/ EZP_CLK	TSI0_CH1	PTA0	UART0_CTS_ b/ UART0_COL_b	FTM0_CH5				JTAG_TCLK/ SWD_CLK	EZP_CLK
23	PTA1	JTAG_TDI/ EZP_DI	TSI0_CH2	PTA1	UARTO_RX	FTM0_CH6				JTAG_TDI	EZP_DI
24	PTA2	JTAG_TDO/ TRACE_SWO/ EZP_DO	TSI0_CH3	PTA2	UARTO_TX	FTM0_CH7				JTAG_TDO/ TRACE_SWO	EZP_DO
25	PTA3	JTAG_TMS/ SWD_DIO	TSI0_CH4	PTA3	UART0_RTS_b	FTM0_CH0				JTAG_TMS/ SWD_DIO	
26	PTA4/ LLWU_P3	NMI_b/ EZP_CS_b	TSI0_CH5	PTA4/ LLWU_P3		FTM0_CH1				NMI_b	EZP_CS_b
27	PTA5	DISABLED		PTA5		FTM0_CH2		CMP2_OUT	I2S0_TX_BCLK	JTAG_TRST_b	
28	PTA12	CMP2_IN0	CMP2_IN0	PTA12	CAN0_TX	FTM1_CH0			I2S0_TXD0	FTM1_QD_ PHA	
29	PTA13/ LLWU_P4	CMP2_IN1	CMP2_IN1	PTA13/ LLWU_P4	CAN0_RX	FTM1_CH1			I2S0_TX_FS	FTM1_QD_ PHB	
30	VDD	VDD	VDD								
31	VSS	VSS	VSS								
32	PTA18	EXTAL0	EXTAL0	PTA18		FTM0_FLT2	FTM_CLKIN0				
33	PTA19	XTAL0	XTALO	PTA19		FTM1_FLT0	FTM_CLKIN1		LPTMR0_ALT1		
34	RESET_b	RESET_b	RESET_b								
35	PTB0/ LLWU_P5	ADC0_SE8/ ADC1_SE8/ TSI0_CH0	ADC0_SE8/ ADC1_SE8/ TSI0_CH0	PTB0/ LLWU_P5	12C0_SCL	FTM1_CH0			FTM1_QD_ PHA		
36	PTB1	ADC0_SE9/ ADC1_SE9/ TSI0_CH6	ADC0_SE9/ ADC1_SE9/ TSI0_CH6	PTB1	I2CO_SDA	FTM1_CH1			FTM1_QD_ PHB		
37	PTB2	ADC0_SE12/ TSI0_CH7	ADC0_SE12/ TSI0_CH7	PTB2	I2C0_SCL	UARTO_RTS_b			FTM0_FLT3		
38	PTB3	ADC0_SE13/ TSI0_CH8	ADC0_SE13/ TSI0_CH8	PTB3	I2C0_SDA	UART0_CTS_ b/ UART0_COL_b			FTM0_FLT0		
39	PTB16	TSI0_CH9	TSI0_CH9	PTB16		UART0_RX		FB_AD17	EWM_IN		
40	PTB17	TSI0_CH10	TSI0_CH10	PTB17		UART0_TX		FB_AD16	EWM_OUT_b		
41	PTB18	TSI0_CH11	TSI0_CH11	PTB18	CAN0_TX	FTM2_CH0	I2S0_TX_BCLK	FB_AD15	FTM2_QD_ PHA		
42	PTB19	TSI0_CH12	TSI0_CH12	PTB19	CAN0_RX	FTM2_CH1	I2S0_TX_FS	FB_OE_b	FTM2_QD_ PHB		



9 Revision History

The following table provides a revision history for this document.

Rev. No.	Date	Substantial Changes
1	3/2012	Initial public release
2	4/2012	 Replaced TBDs throughout. Updated "Power consumption operating behaviors" table. Updated "ADC electrical specifications" section. Updated "VREF full-range operating behaviors" table. Updated "I2S/SAI Switching Specifications" section. Updated "TSI electrical specifications" table.
3	11/2012	 Updated orderable part numbers. Updated the maximum input voltage (V_{ADIN}) specification in the "16-bit ADC operating conditions" section.

Table 46. Revision History